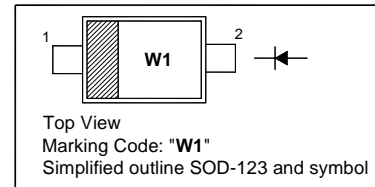


Silicon Epitaxial Planar Switching Diode
Features

- SOD-123 package
- Fast switching
- These diodes are also available in other case style including the DO-35 case with the type designation 1N4148, the MiniMELF case with the type designation LL4148 and the MicroMELF case with the type designation MCL4148.

PINNING

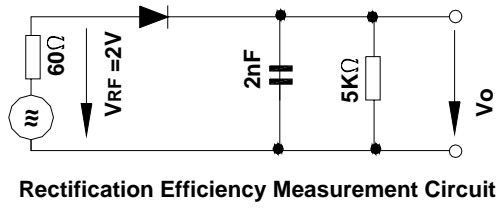
PIN	DESCRIPTION
1	Cathode
2	Anode


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

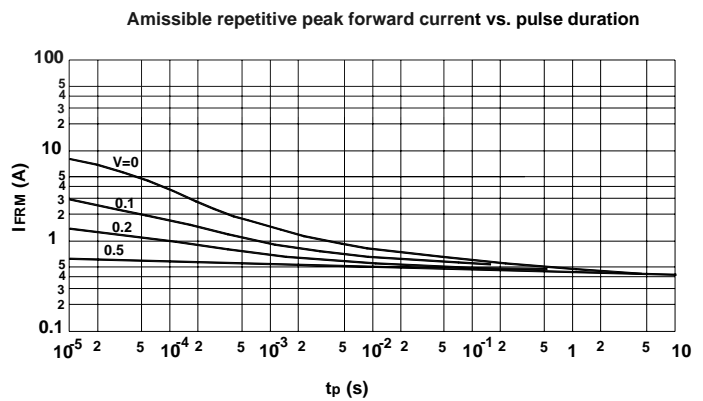
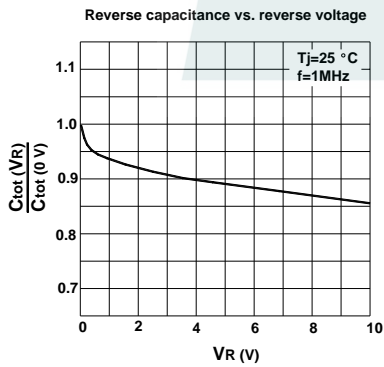
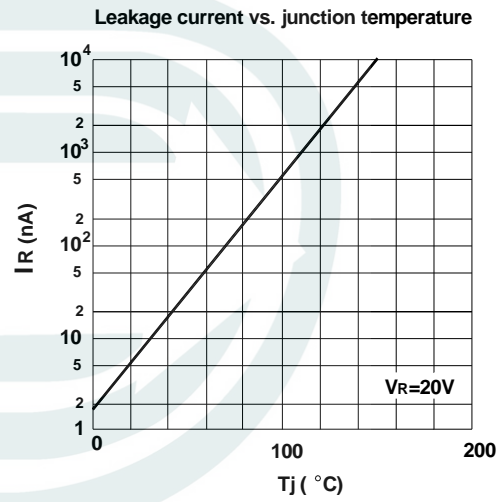
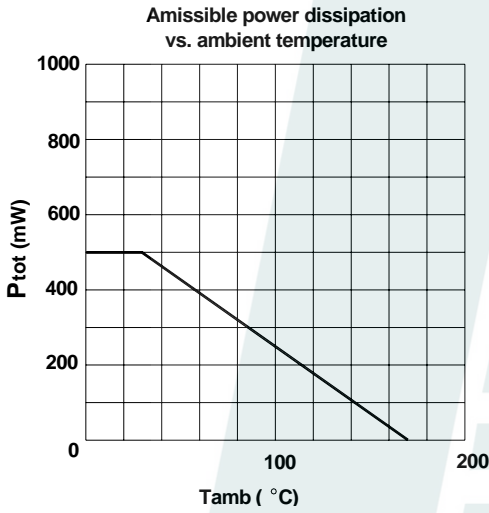
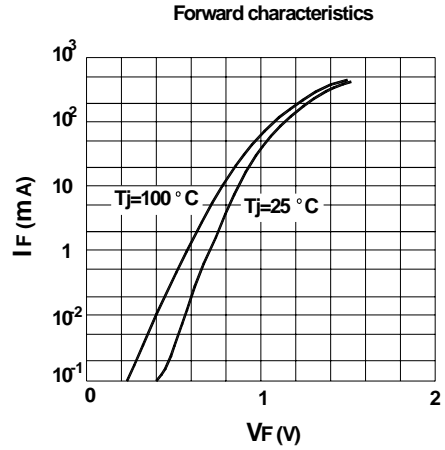
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Non-repetitive Peak Forward Surge Current at $t = 1\text{ }\mu\text{s}$	I_{FSM}	2	A
Power Dissipation	P_{tot}	400	mW
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	312	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	1	V
Reverse Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}, T_J = 150\text{ }^\circ\text{C}$	I_R	25 5 50	nA μA μA
Total Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_{tot}	4	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$ to $I_R = 1\text{ mA}, V_R = 6\text{ V}, R_L = 100\text{ }\Omega$	t_{rr}	4	ns



Rectification Efficiency Measurement Circuit



Inquire@party-itl.com



ISO/TS 16949 : 2009 Certificate No. 05103
 ISO14001 : 2004 Certificate No. 7116
 ISO 9001 : 2008 Certificate No. 090998
 BS-OHSAS 18001 : 2007 Certificate No. 7116
 IECQ QC 080000 Certificate No. PCC-HP84148-1

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123

